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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT:
SERIAL NO.
FILING DATE:
INVENTION:

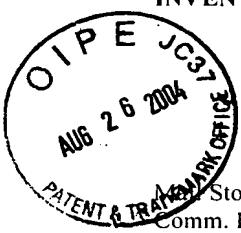
Kobayashi, T. et al.
10/813,528
March 30, 2004

ATTORNEY DOCKET NO. 09794353-0033
GROUP ART UNIT: 2726

EXAMINER: Not yet assigned

METHOD FOR PRODUCING STRUCTURED SUBSTRATE, STRUCTURED SUBSTRATE,
METHOD FOR PRODUCING SEMICONDUCTOR LIGHT EMITTING DEVICE,
SEMICONDUCTOR LIGHT EMITTING DEVICE, METHOD FOR PRODUCING
SEMICONDUCTOR DEVICE, SEMICONDUCTOR DEVICE, METHOD FOR PRODUCING
DEVICE AND DEVICE

INFORMATION DISCLOSURE STATEMENT TRANSMITTAL LETTER



Stop Amendment

Comm. For Patents

Alexandria, VA 22313-1450

Sir:

Submitted herewith is an Information Disclosure Statement for consideration in the above-identified application. This Information Disclosure Statement is submitted:

Within 3 months (1) of filing date of a national application; (2) of date of entry of the national stage as set forth in 37 C.F.R. §1.491 in an international application; or (3) before the mailing date of a first Office Action on the merits, whichever occurs last. (No fee is required.)

After the mailing date of a first Office Action but before (1) mailing of a final action under 37 C.F.R. §1.113; or (2) mailing of a notice of allowance under §1.311, whichever occurs first.

Payment for the fee set forth in 37 C.F.R. §1.17(p) accompanies this submission; or

The certification specified in 37 C.F.R. §1.97(e) is made below. (No fee is required.)

After the mailing of (1) a final action under 37 C.F.R. §1.113; or (2) a notice of allowance under 37 C.F.R. §1.311 whichever occurs first, but **before** payment of the issue fee. The certification specified in 37 C.F.R. §1.97(e) is made below. The Commissioner hereby is petitioned to consider the Information Disclosure Statement accompanying this submission. Payment for the Petition fee set forth in 37 C.F.R. §1.17(i)(1) accompanies this submission.

The undersigned counsel for applicant(s) hereby certifies each item of information identified in the Information Disclosure Statement was cited in a communication from a foreign Patent Office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.

The undersigned counsel for applicant(s) hereby certifies that no item of information contained in the Information Disclosure Statement was cited in a communication from a foreign Patent Office in a counterpart foreign application, or to the knowledge of the undersigned, after making reasonable inquiry, was known to any individual designated in 37 C.F.R. §1.56(c) more than three months prior to the filing of this Information Disclosure Statement.

Payment by Credit Card. PTO Form 2038 in the amount of \$180.00 is enclosed.

The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment to Account No. 19-3140. *A duplicate copy of this sheet is enclosed for this purpose.*

Very respectfully,

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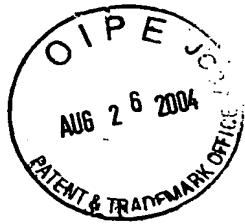
Telephone (312) 876-8000

CERTIFICATE OF MAILING

I hereby certify that this Information Disclosure Statement is being deposited with the United States Postal Service as in an envelope addressed to Mail Stop Amendment, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450 via first class mail on August 23, 2004

Paula M. Theismann

Paula M. Theismann



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT

APPLICANT(S): Kobayashi, T.. et al.

DOCKET NO.: 09794353-0033

SERIAL NO.: 10/813,528

GROUP ART UNIT: 2726

DATE FILED: March 30, 2004

EXAMINER: Not yet assigned

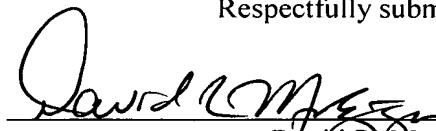
INVENTION: METHOD FOR PRODUCING STRUCTURED SUBSTRATE, STRUCTURED SUBSTRATE, METHOD FOR PRODUCING SEMICONDUCTOR LIGHT EMITTING DEVICE, SEMICONDUCTOR LIGHT EMITTING DEVICE, METHOD FOR PRODUCING SEMICONDUCTOR DEVICE, SEMICONDUCTOR DEVICE, METHOD FOR PRODUCING DEVICE AND DEVICE

Mail Stop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

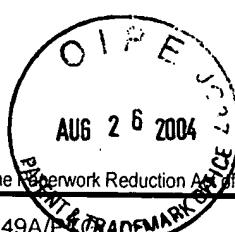
SIR:

In accordance with the provisions of 37 C.F.R. § 1.56, Applicants request that citation and examination of the reference identified on the attached PTO-1449 form, a copy of which is enclosed herewith in accordance with 37 C.F.R. §1.98, be made during the course of examination of the above-referenced application for United States Letters Patent. The above-identified patent application is based upon this Japanese reference to which priority was not claimed.

Respectfully submitted by,



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Substitute for form 1449A/

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 1

<i>Complete if Known</i>	
Application Number	10/813,528
Filing Date	March 30, 2004
First Named Inventor	Kobayashi, T.
Group Art Unit	2726
Examiner Name	Not yet assigned
Attorney Docket Number	09794353-0033

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
		JP 2003-124115	04/24/2003	Sony Corporation		<input type="checkbox"/>
						<input type="checkbox"/>
						<input type="checkbox"/>
						<input type="checkbox"/>
						<input type="checkbox"/>

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

METHOD OF MANUFACTURING STRUCTURE BOARD, STRUCTURE BOARD, METHOD OF MANUFACTURING SEMICONDUCTOR LIGHT EMITTING DEVICE, SEMICONDUCTOR LIGHT EMITTING DEVICE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, SEMICONDUCTOR DEVICE, METHOD OF MANUFACTURING DEVICE, AND DEVICE

Publication Number: 2003-124115 (JP 2003124115 A) , April 25, 2003

Inventors:

- KOBAYASHI TOSHIMASA
- MOTOKI KENSAKU

Applicants

- SUMITOMO ELECTRIC IND LTD
- SONY CORP

Application Number: 2001-315705 (JP 2001315705) , October 12, 2001

International Class:

- H01L-021/20
- H01L-033/00
- H01S-005/323

Abstract:

PROBLEM TO BE SOLVED: To provide a semiconductor light emitting device which is superior in characteristics such as light emission characteristics and high in reliability and has a long service life and a semiconductor device which is superior in characteristics and reliability and has a long service life. SOLUTION: Second regions B having second average dislocation density higher than a first region A which is formed of crystal having a first average dislocation density are regularly arranged in the first region A on a nitride III-V compound semiconductor substrate 1. When a semiconductor light emitting device or a semiconductor device is manufactured by the use of the above nitride III-V compound semiconductor substrate 1, the light emitting region of the semiconductor light emitting device or the active region of the semiconductor device is formed so as to avoid the second regions B. COPYRIGHT: (C)2003,JPO

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